

TO-92 Plastic-Encapsulate Transistors

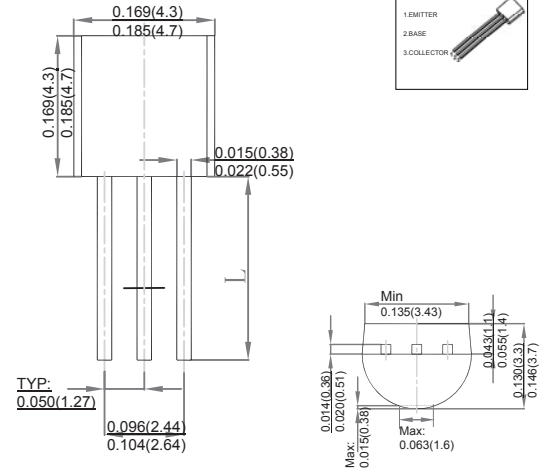
FEATURES

- Power Amplifier
- TRANSISTOR (NPN)

MECHANICAL DATA

- Case style: TO-92 molded plastic
- Mounting position: any

TO-92



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	80	V
V_{CE0}	Collector-Emitter Voltage	80	V
V_{EB0}	Emitter-Base Voltage	4	V
I_C	Collector Current -Continuous	0.5	A
P_D	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	200	°C /W
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55 ~ +150	°C

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	80		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	80		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	4		V
Collector cut-off current	I_{CBO}	$V_{CB}=80V, I_E=0$		0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=60V, I_B=0$		0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=3V, I_C=0$		0.1	μA
DC current gain	h_{FE1}	$V_{CE}=1V, I_C=100mA$	100	400	
	h_{FE2}	$V_{CE}=1V, I_C=10mA$	100		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100mA, I_B=10mA$		0.25	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100mA, I_B=10mA$		1.2	V
Transition frequency	f_T	$V_{CE}=2V, I_C=10mA$ $f=100MHz$	100		MHz

Marking	MPSA06
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Typical Characteristics

